Athanasios Dimoulas

List of Publications by Year
in descending order

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184	5,463	70961	98622
papers	citations	41 h-index	67 g-index

192	192	192	5655
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Ultrafast Spinâ€Charge Conversion at SnBi₂Te₄/Co Topological Insulator Interfaces Probed by Terahertz Emission Spectroscopy. Advanced Optical Materials, 2022, 10, .	3.6	13
2	Magnetic skyrmion manipulation in CrTe2/WTe2 2D van der Waals heterostructure. Applied Physics Letters, 2022, 120, .	1.5	10
3	Hf_{0.5}Zr_{0.5}O₂-Based Germanium Ferroelectric p-FETs for Nonvolatile Memory Applications. ACS Applied Electronic Materials, 2022, 4, 2815-2821.	2.0	10
4	Layer-by-layer assembled graphene coatings on polyurethane films as He permeation barrier. Progress in Organic Coatings, 2021, 150, 105984.	1.9	13
5	The Role of Interface Defect States in nâ€and pâ€Type Ge Metalâ€“Ferroelectricâ€“Semiconductor Structures with Hf_{0.5}Zr_{0.5}O₂ Ferroelectric. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000500.	0.8	3
6	Topological surface states in epitaxial <mml:math		

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19	Advanced Photocatalysts Based on Reduced Nanographene Oxideâ€“TiO2 Photonic Crystal Films. Materials, 2019, 12, 2518.	1.3	10
20	Direct versus reverse vertical two-dimensional Mo₂C/graphene heterostructures for enhanced hydrogen evolution reaction electrocatalysis. Nanotechnology, 2019, 30, 415404.	1.3	26
21	Room Temperature Commensurate Charge Density Wave in Epitaxial Strained TiTe₂ Multilayer Films. Advanced Materials Interfaces, 2019, 6, 1801850.	1.9	34
22	Surface-Enhanced Raman Spectroscopy of Graphene Integrated in Plasmonic Silicon Platforms with Three-Dimensional Nanotopography. Journal of Physical Chemistry C, 2019, 123, 3076-3087.	1.5	16
23	Very large remanent polarization in ferroelectric Hf1-xZrxO2 grown on Ge substrates by plasma assisted atomic oxygen deposition. Applied Physics Letters, 2019, 114, .	1.5	37
24	Atmospheric pressure plasma directed assembly during photoresist removal: A new route to micro and nano pattern formation. Micro and Nano Engineering, 2019, 3, 15-21.	1.4	10
25	Mo₂C/graphene heterostructures: low temperature chemical vapor deposition on liquid bimetallic Snâ€“Cu and hydrogen evolution reaction electrocatalytic properties. Nanotechnology, 2019, 30, 125401.	1.3	44
26	Topological band crossings in epitaxial strained SnTe. Physical Review Materials, 2019, 3, .	0.9	6
27	Surface-enhanced Raman Spectroscopy of Graphene Integrated in Three-dimensional Nanostructured Plasmonic Silicon Platforms. , 2019, , .		0
28	Massless Dirac Fermions in ZrTe₂ Semimetal Grown on InAs(111) by van der Waals Epitaxy. ACS Nano, 2018, 12, 1696-1703.	7.3	82
29	Insight and control of the chemical vapor deposition growth parameters and morphological characteristics of graphene/Mo 2 C heterostructures over liquid catalyst. Journal of Crystal Growth, 2018, 495, 46-53.	0.7	40
30	Direct Observation at Room Temperature of the Orthorhombic Weyl Semimetal Phase in Thin Epitaxial MoTe₂. Advanced Functional Materials, 2018, 28, 1802084.	7.8	31
31	Molecular beam epitaxy of thin HfTe ₂ semimetal films. 2D Materials, 2017, 4, 015001.	2.0	55
32	Graphene by one-step chemical vapor deposition from ferrocene vapors: Properties and electrochemical evaluation. Journal of Applied Physics, 2016, 119, .	1.1	13
33	Epitaxial 2D SnSe₂/ 2D WSe₂ van der Waals Heterostructures. ACS Applied Materials & Interfaces, 2016, 8, 23222-23229.	4.0	94
34	Strain dependence of band gaps and exciton energies in pure and mixed transition-metal dichalcogenides. Physical Review B, 2016, 94, .	1.1	94
35	Negative Quantum Capacitance Effects in Metalâ€“Insulatorâ€“Semiconductor Devices with Composite Grapheneâ€Encapsulated Gates. Advanced Electronic Materials, 2016, 2, 1500297.	2.6	6
36	Experimental investigation of metallic thin film modification of nickel substrates for chemical vapor deposition growth of single layer graphene at low temperature. Applied Surface Science, 2016, 385, 554-561.	3.1	12

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37	AB stacked few layer graphene growth by chemical vapor deposition on single crystal Rh(1 1 1) and electronic structure characterization. Applied Surface Science, 2016, 369, 251-256.	3.1	17
38	Evidence for Germanene growth on epitaxial hexagonal (h)-AlN on Ag(1 1 1). Journal of Physics Condensed Matter, 2016, 28, 045002.	0.7	57
39	Epitaxial 2D MoSe₂ (HfSe₂) Semiconductor/2D TaSe₂ Metal van der Waals Heterostructures. ACS Applied Materials & Interfaces, 2016, 8, 1836-1841.	4.0	60
40	Silicene: a review of recent experimental and theoretical investigations. Journal of Physics Condensed Matter, 2015, 27, 253002.	0.7	180
41	Epitaxial ZrSe2/MoSe2 semiconductor v.d. Waals heterostructures on wide band gap AlN substrates. Microelectronic Engineering, 2015, 147, 269-272.	1.1	42
42	Two-dimensional semiconductor HfSe2 and MoSe2/HfSe2 van der Waals heterostructures by molecular beam epitaxy. Applied Physics Letters, 2015, 106, .	1.5	110
43	High-quality, large-area MoSe₂ and MoSe₂/Bi₂Se₃ heterostructures on AlN(0001)/Si(111) substrates by molecular beam epitaxy. Nanoscale, 2015, 7, 7896-7905.	2.8	122
44	Reducing the layer number of AB stacked multilayer graphene grown on nickel by annealing at low temperature. Nanotechnology, 2015, 26, 405603.	1.3	6
45	Silicene and germanene: Silicon and germanium in the â€œflatlandâ€• Microelectronic Engineering, 2015, 131, 68-78.	1.1	72
46	(Invited) Interface Engineering Routes for a Future CMOS Ge-Based Technology. ECS Transactions, 2014, 61, 73-88.	0.3	2
47	Silicene on metal substrates: A first-principles study on the emergence of a hierarchy of honeycomb structures. Applied Surface Science, 2014, 291, 93-97.	3.1	24
48	Ge interface engineering using ultra-thin La2O3 and Y2O3 films: A study into the effect of deposition temperature. Journal of Applied Physics, 2014, 115, .	1.1	47
49	Observation of Surface Dirac Cone in High-Quality Ultrathin Epitaxial Bi₂Se₃ Topological Insulator on AlN(0001) Dielectric. ACS Nano, 2014, 8, 6614-6619.	7.3	37
50	Surface electronic bands of submonolayer Ge on Ag(111). Physical Review B, 2013, 88, .	1.1	36
51	Room temperature analysis of Ge p+/n diodes reverse characteristics fabricated by platinum assisted dopant activation. Solid-State Electronics, 2013, 81, 19-26.	0.8	2
52	Inorganicâ€“organic coreâ€“shell titania nanoparticles for efficient visible light activated photocatalysis. Applied Catalysis B: Environmental, 2013, 130-131, 14-24.	10.8	87
53	Electronic band structure imaging of three layer twisted graphene on single crystal Cu(111). Applied Physics Letters, 2013, 103, 213108.	1.5	8
54	Evidence for graphite-like hexagonal AlN nanosheets epitaxially grown on single crystal Ag(111). Applied Physics Letters, 2013, 103, .	1.5	251

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55	Evidence for hybrid surface metallic band in (4â€‰Ã—â€‰4) silicene on Ag(111). Applied Physics Letters, 2013, 103, .	1.3	122
56	Interaction of metal impurities with native oxygen defects in GeO2. Microelectronic Engineering, 2013, 104, 37-41.	1.1	9
57	Gate stack dielectric degradation of rare-earth oxides grown on high mobility Ge substrates. Journal of Applied Physics, 2012, 112, .	1.1	23
58	Defect configurations of high-k cations in germanium. Journal of Applied Physics, 2012, 111, 023714.	1.1	15
59	Interaction of oxygen vacancies in yttrium germanates. Physical Chemistry Chemical Physics, 2012, 14, 14630.	1.3	11
60	Structural evolution of single-layer films during deposition of silicon on silver: a first-principles study. Journal of Physics Condensed Matter, 2012, 24, 442001.	0.7	38
61	Strain-induced changes to the electronic structure of germanium. Journal of Physics Condensed Matter, 2012, 24, 195802.	0.7	67
62	Impurity diffusion, point defect engineering, and surface/interface passivation in germanium. Annalen Der Physik, 2012, 524, 123-132.	0.9	29
63	Electrical reliability characteristics and dielectrics degradation in gate stacks (REO-HfO<inf>2</inf>) grown on the high mobility Ge substrates. , 2011, , .		0
64	Impact of post deposition annealing in the electrically active traps at the interface between Ge(001) substrates and LaGeOx films grown by molecular beam deposition. Journal of Applied Physics, 2011, 110, 084504.	1.1	8
65	The effect of Se and Se/Al passivation on the oxidation of Ge. Microelectronic Engineering, 2011, 88, 407-410.	1.1	8
66	Ge-related impurities in high-k oxides: Carrier traps and interaction with native defects. Microelectronic Engineering, 2011, 88, 1432-1435.	1.1	5
67	Ge volatilization products in high-k gate dielectrics. Microelectronic Engineering, 2011, 88, 427-430.	1.1	14
68	High performance n+/p and p+/n germanium diodes at low-temperature activation annealing. Microelectronic Engineering, 2011, 88, 254-261.	1.1	7
69	Current instabilities in rare-earth oxides-HfO2 gate stacks grown on germanium based metal-oxide-semiconductor devices due to Maxwellâ€“Wagner instabilities and dielectrics relaxation. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 01AB06.	0.6	3
70	Atomic scale mechanism for the Ge-induced stabilization of the tetragonal, very high-Î², phase of ZrO2. Applied Physics Letters, 2011, 99, .	1.5	15
71	(Invited) Active Trap Determination at the Interface of Ge and In0.53Ga0.47 as Substrates with Dielectric Layers. ECS Transactions, 2011, 41, 203-221.	0.3	3
72	A Deep-Level Transient Spectroscopy Study of Implanted Ge p+n and n+p Junctions by Pt-Induced Crystallization. ECS Transactions, 2011, 41, 299-308.	0.3	1

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73	Structural and electrical properties of HfO2/Dy2O3 gate stacks on Ge substrates. Thin Solid Films, 2010, 518, 3964-3971.	0.8	13
74	SILC decay in La2O3 gate dielectrics grown on Ge substrates subjected to constant voltage stress. Solid-State Electronics, 2010, 54, 979-984.	0.8	9
75	(Invited) Ge Surfaces and Its Passivation by Rare Earth Lanthanum Germanate Dielectric. ECS Transactions, 2010, 33, 433-446.	0.3	4
76	Maxwell-Wagner Instabilities and Defects Generation during CVS in REO-HfO₂ Gate Stacks Grown on Germanium Based MOS Devices. ECS Transactions, 2010, 33, 367-374.	0.3	2
77	Chemical stability of lanthanum germanate passivating layer on Ge upon high-k deposition: A photoemission study on the role of La in the interface chemistry. Journal of Applied Physics, 2010, 108, 064115.	1.1	20
78	The role of La surface chemistry in the passivation of Ge. Applied Physics Letters, 2010, 96, .	1.5	51
79	Stabilization of very high-k tetragonal phase in Ge-doped ZrO2 films grown by atomic oxygen beam deposition. Journal of Applied Physics, 2009, 106, .	1.1	36
80	Metal-induced low temperature activation and La<inf>2</inf>O<inf>3</inf> passivation of germanium N⁺/P and P⁺/N Junctions. , 2009, , .		0
81	Defects Generation under Constant Voltage Stress in La₂O₃/HfO₂ Gate Stacks Grown on Ge Substrates. ECS Transactions, 2009, 25, 105-111.	0.3	1
82	Metal-oxide-semiconductor devices on p-type Ge with La[sub 2]O[sub 3] and ZrO[sub 2]/La[sub 2]O[sub 3] as gate dielectric and the effect of postmetallization anneal. Journal of Vacuum Science & Technology B, 2009, 27, 246.	1.3	9
83	Source and Drain Contacts for Germanium and IIIâ€“V FETs for Digital Logic. MRS Bulletin, 2009, 34, 522-529.	1.7	42
84	Correlation of Charge Buildup and Stress-Induced Leakage Current in Cerium Oxide Films Grown on Ge (100) Substrates. IEEE Transactions on Electron Devices, 2009, 56, 399-407.	1.6	29
85	Study of stress-induced leakage current (SILC) in HfO2/Dy2O3 high-Î² gate stacks on germanium. Microelectronics Reliability, 2009, 49, 26-31.	0.9	7
86	Stabilization of a very high-k tetragonal ZrO2 phase by direct doping with germanium. Microelectronic Engineering, 2009, 86, 1626-1628.	1.1	27
87	Germanium surface and interfaces (Invited Paper). Microelectronic Engineering, 2009, 86, 1577-1581.	1.1	21
88	Lanthanum germanate as dielectric for scaled Germanium metalâ€“oxideâ€“semiconductor devices. Microelectronic Engineering, 2009, 86, 1635-1637.	1.1	12
89	Investigation of voltage dependent relaxation, charge trapping, and stress induced leakage current effects in HfO2â•Dy2O3 gate stacks grown on Ge (100) substrates. Journal of Vacuum Science & Technology B, 2009, 27, 439-442.	1.3	13
90	Modeling of negatively charged states at the Ge surface and interfaces. Applied Physics Letters, 2009, 94, .	1.5	95

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91	Current Transport Mechanism in High-Î¤ Cerium Oxide Gate Dielectrics Grown on Germanium Substrates. Electrochemical and Solid-State Letters, 2009, 12, H165.	2.2	24
92	Impact of La<inf>2</inf>O<inf>3</inf> Thickness on HfO<inf>2</inf>/La<inf>2</inf>O<inf>3</inf>/Ge capacitors and p-channel MOSFETs. , 2009, , .		1
93	SILC decay in Ge-based MOS devices with La<inf>2</inf>O<inf>3</inf> gate dielectrics subjected to constant voltage stress. , 2009, , .		1
94	Nanoscale electrical characterization of ultrathin high-k dielectric MOS stacks: A conducting AFM study. Materials Science in Semiconductor Processing, 2008, 11, 250-253.	1.9	3
95	Electrical properties of La2O3 and HfO2â^•La2O3 gate dielectrics for germanium metal-oxide-semiconductor devices. Journal of Applied Physics, 2008, 103, .	1.1	108
96	Ge p-channel MOSFETS with La₂O₃ and Al₂O₃ gate dielectrics. , 2008, , .		4
97	Post-stress/breakdown leakage mechanism in ultrathin high-Î¤ (HfO₂)_x(SiO₂)_{1-x}/SiO₂gate stacks: A nanoscale conductive-Atomic Force Microscopy C-AFM. Materials Research Society Symposia Proceedings, 2008, 1108, 1.	0.1	0
98	Anomalous charge trapping dynamics in cerium oxide grown on germanium substrate. Journal of Applied Physics, 2008, 103, 064514.	1.1	20
99	Beneficial effect of La on band offsets in Ge/high-Î¤ insulator structures with GeO2 and La2O3 interlayers. Applied Physics Letters, 2008, 93, 102115.	1.5	16
100	Germanium-induced stabilization of a very high-k zirconia phase in ZrO2/GeO2 gate stacks. Applied Physics Letters, 2008, 93, 082904.	1.5	59
101	Very high-Î¤â€^ZrO2 with La2O3â€^(LaGeOx) passivating interfacial layers on germanium substrates. Applied Physics Letters, 2008, 93, .	1.5	55
102	Gate Dielectrics for High Mobility Semiconductors. ECS Transactions, 2008, 16, 295-306.	0.3	3
103	Very High-k Tetragonal ZrO2 on Ge with GeO2 Passivating Interfacial Layer. ECS Transactions, 2008, 16, 767-772.	0.3	1
104	Materials and electrical characterization of molecular beam deposited CeO2 and CeO2/HfO2 bilayers on germanium. Journal of Applied Physics, 2007, 102, .	1.1	48
105	Conduction band offset of HfO2 on GaAs. Applied Physics Letters, 2007, 91, .	1.5	46
106	Total Dose Response of Ge MOS Capacitors With HfO$_{2}$/Dy$_{2}$O$_{3}$ Gate Stacks. IEEE Transactions on Nuclear Science, 2007, 54, 971-974.	1.2	22
107	Rare earth oxides as high-k dielectrics for Ge based MOS devices: An electrical study of Pt/Gd2O3/Ge capacitors. Solid-State Electronics, 2007, 51, 164-169.	0.8	23
108	Germanium FETs and capacitors with rare earth CeO2/HfO2 gates. Solid-State Electronics, 2007, 51, 1508-1514.	0.8	21

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109	Epitaxial germanium-on-insulator grown on (001) Si. Microelectronic Engineering, 2007, 84, 2328-2331.	1.1	36
110	Germanium metal-insulator-semiconductor capacitors with rare earth La2O3 gate dielectric. Microelectronic Engineering, 2007, 84, 2324-2327.	1.1	28
111	In-situ MBE Si as passivating interlayer on GaAs for HfO2 MOSCAPâ€™s: effect of GaAs surface reconstruction. Microelectronic Engineering, 2007, 84, 2142-2145.	1.1	13
112	Germanium MOSFETs With $hbox{CeO}_{2}/hbox{HfO}_{2}/ hbox{TiN}$ Gate Stacks. IEEE Transactions on Electron Devices, 2007, 54, 1425-1430.	1.6	37
113	Determining weak Fermi-level pinning in MOS devices by conductance and capacitance analysis and application to GaAs MOS devices. Solid-State Electronics, 2007, 51, 1101-1108.	0.8	18
114	Interface engineering for Ge metal-oxideâ€“semiconductor devices. Thin Solid Films, 2007, 515, 6337-6343.	0.8	87
115	Post deposition annealing studies of lanthanum aluminate and ceria high-k dielectrics on germanium. Microelectronics Reliability, 2007, 47, 532-535.	0.9	16
116	Fermi-level pinning and charge neutrality level in germanium. Applied Physics Letters, 2006, 89, 252110.	1.5	532
117	Germanium FETs and capacitors with rare earth CeO2/HfO2 gates. , 2006, , .		1
118	Current Challenges in Ge MOS Technology. ECS Transactions, 2006, 3, 371-384.	0.3	9
119	HfO2 as gate dielectric on Ge: Interfaces and deposition techniques. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 135, 256-260.	1.7	68
120	Impact of germanium surface passivation on the leakage current of shallow planar pâ€“n junctions. Materials Science in Semiconductor Processing, 2006, 9, 716-720.	1.9	18
121	Electrical Properties of Atomic-Beam Deposited GeO[sub 1âˆ’x]N[sub x]âˆ•HfO[sub 2] Gate Stacks on Ge. Journal of the Electrochemical Society, 2006, 153, G1112.	1.3	15
122	Germanium diffusion during HfO2 growth on Ge by molecular beam epitaxy. Applied Physics Letters, 2006, 89, 122906.	1.5	22
123	Electron energy band alignment at interfaces of (100)Ge with rare-earth oxide insulators. Applied Physics Letters, 2006, 88, 132111.	1.5	52
124	Electrical properties of as-grown molecular beam epitaxy high-k gate dielectrics deposited on silicon. Journal of Applied Physics, 2006, 99, 064105.	1.1	8
125	Band alignment at the La2Hf2O7âˆ•(001)Si interface. Applied Physics Letters, 2006, 88, 202903.	1.5	31
126	Subnanometer-equivalent-oxide-thickness germanium p-metal-oxide-semiconductor field effect transistors fabricated using molecular-beam-deposited high-k/metal gate stack. Applied Physics Letters, 2006, 88, 132107.	1.5	70

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127	Characterization of field-effect transistors with La2Hf2O7 and HfO2 gate dielectric layers deposited by molecular-beam epitaxy. Journal of Applied Physics, 2006, 99, 024508.	1.1	35
128	ELECTRICALLY ACTIVE INTERFACE AND BULK SEMICONDUCTOR DEFECTS IN HIGH-K / GERMANIUM STRUCTURES. , 2006, , 237-248.		14
129	Interface trap density in amorphous La2Hf2O7/SiO2 high-Î¤ gate stacks on Si. Applied Physics A: Materials Science and Processing, 2005, 80, 253-257.	1.1	18
130	Short minority carrier response time in HfO2 /Ge metal-insulator-semiconductor capacitors. Microelectronic Engineering, 2005, 80, 34-37.	1.1	7
131	Space-charge-limited current involving carrier injection into impurity bands of high-k insulators. Applied Physics Letters, 2005, 86, 203506.	1.5	7
132	HfO2 high-k dielectrics grown on (100)Ge with ultrathin passivation layers: Structure and interfacial stability. Applied Physics Letters, 2005, 87, 221906.	1.5	46
133	HfO2 high-Î¤ gate dielectrics on Ge (100) by atomic oxygen beam deposition. Applied Physics Letters, 2005, 86, 032908.	1.5	144
134	X-ray absorption study of the growth ofY2O3on Si(001). Physical Review B, 2005, 71, .	1.1	23
135	Intrinsic carrier effects in HfO2â€“Ge metalâ€“insulatorâ€“semiconductor capacitors. Applied Physics Letters, 2005, 86, 223507.	1.5	54
136	Molecular-beam Deposition of High-k Gate Dielectrics for Advanced CMOS. , 2005, , 3-15.		5
137	Complex admittance analysis for La2Hf2O7/SiO2 high-Î¤ dielectric stacks. Applied Physics Letters, 2004, 84, 260-262.	1.5	61
138	La2Hf2O7 high-Î¤ gate dielectric grown directly on Si(001) by molecular-beam epitaxy. Applied Physics Letters, 2004, 85, 3205-3207.	1.5	57
139	Si overgrowth on Y2O3 (1 1 0)/Si (0 0 1) by molecular beam epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 109, 39-41.	1.7	5
140	EELS study of oxygen superstructure in epitaxial Y2O3 layers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 109, 52-55.	1.7	8
141	MBE lanthanum-based high-k gate dielectrics as candidates for SiO2 gate oxide replacement. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 109, 85-88.	1.7	37
142	Electrical properties of metalâ€“oxideâ€“silicon structures with LaAlO3 as gate oxide. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 109, 94-98.	1.7	7
143	Ru and RuO2 gate electrodes for advanced CMOS technology. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 109, 117-121.	1.7	52
144	Spin dependent Andreev reflection in ferromagnetic/insulator/d-wave superconductor ballistic junctions. Physica C: Superconductivity and Its Applications, 2004, 405, 77-83.	0.6	4

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145	Effects on surface morphology of epitaxial Y2O3 layers on Si (001) after postgrowth annealing. Thin Solid Films, 2004, 468, 303-309.	0.8	41
146	Structural characterization of epitaxial Y2O3 on Si (0 0 1) and of the Y2O3/Si interface. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 109, 47-51.	1.7	4
147	Oxygen vacancy ordering in epitaxial layers of yttrium oxide on Si (001). Applied Physics Letters, 2003, 82, 4053-4055.	1.5	53
148	Electrical properties of Y2O3 high-Î¹ gate dielectric on Si(001): The influence of postmetallization annealing. Journal of Applied Physics, 2003, 93, 3982-3989.	1.1	35
149	High epitaxial quality Y2O3 high-Î¹ dielectric on vicinal Si(001) surfaces. Applied Physics Letters, 2002, 81, 3549-3551.	1.5	47
150	Structural Quality And Electrical Behavior Of Epitaxial High-Î¹ Y2O3 / Si(001). Materials Research Society Symposia Proceedings, 2002, 745, 9101/T7.10.1.	0.1	0
151	Structural Quality and Electrical Behavior of Epitaxial High-k Y2O3 / Si(001). Materials Research Society Symposia Proceedings, 2002, 747, 1.	0.1	0
152	Structural and electrical quality of the high-k dielectric Y2O3 on Si (001): Dependence on growth parameters. Journal of Applied Physics, 2002, 92, 426-431.	1.1	82
153	Epitaxial issues and growth morphologies of InAlAs/InGaAs heterostructures on non-(100) InP index substrates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 87, 249-255.	1.7	1
154	Direct heteroepitaxy of crystalline Y2O3 on Si (001) for high-k gate dielectric applications. Journal of Applied Physics, 2001, 90, 4224-4230.	1.1	62
155	EPITAXIAL Y₂O₃ ON Si (001) BY MBE FOR HIGH-k GATE DIELECTRIC APPLICATIONS. , 2001, , .		0
156	Barrier-induced enhancement of Andreev reflection for minority-spin quasiparticles in ferromagnetic metal/insulator/superconductor ballistic junctions. Physical Review B, 2000, 61, 9729-9733.	1.1	14
157	Enhancement of 2D growth of MBE hetero-structures using laser-assisted MBE techniques. Thin Solid Films, 1998, 318, 22-28.	0.8	0
158	Materials interfaces in flip chip interconnects for optical components; performance and degradation mechanisms. Microelectronics Reliability, 1998, 38, 1307-1312.	0.9	2
159	<title>Processing of free-space optical interconnect devices using solder engineering</title>. , 1998, 3288, 262.		0
160	<title>GaAs-on-Si MSM photodetector: FET receiver characterization and reliability</title>. , 1998, 3288, 53.		0
161	Failure mechanisms of GaAs mesfets with Cu/refractory metallized gates. Microelectronics Reliability, 1997, 37, 1699-1702.	0.9	1
162	Transport through a 2DEG channel with superconducting boundaries. Surface Science, 1996, 361-362, 320-323.	0.8	0

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163	Electron density effects in the modulation spectroscopy of strained and latticeâ€matched InGaAs/InAlAs/InP highâ€electronâ€mobility transistor structures. Journal of Applied Physics, 1996, 80, 3484-3487.	1.1	13
164	Electron Density Effects in the Modulation Spectroscopy of Strained and Lattice-Matched InGaAs/InAlAs/InP HEMTs.. Materials Research Society Symposia Proceedings, 1995, 406, 301.	0.1	0
165	Photoluminescence studies of modulation-doped strained multiple quantum wells. Journal of Crystal Growth, 1995, 152, 28-33.	0.7	9
166	Phase-Dependent Resistance in a Superconductor-Two-Dimensional-Electron-Gas Quasiparticle Interferometer. Physical Review Letters, 1995, 74, 602-605.	2.9	118
167	Optical and transport properties of Î´-doped pseudomorphic AlGaAs/InGaAs/GaAs structures. Journal of Infrared, Millimeter and Terahertz Waves, 1994, 15, 1809-1818.	0.6	1
168	Supercurrent transport and quasiparticle interference in a mesoscopic two-dimensional electron gas coupled to superconductors. Physica B: Condensed Matter, 1994, 203, 285-290.	1.3	21
169	Electric field dependence of allowed and forbidden transitions in In0.53Ga0.47As/In0.52Al0.48As single quantum wells by room temperature modulation spectroscopy. Applied Surface Science, 1993, 63, 191-196.	3.1	1
170	Materials problems for the development of InGaAs/InAlAs HEMT technology. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1993, 20, 21-25.	1.7	1
171	Interband transitions inInxGa1â^'xAs/In0.52Al0.48As single quantum wells studied by room-temperature modulation spectroscopy. Physical Review B, 1993, 47, 7198-7207.	1.1	15
172	Degenerate electron gas effects in the modulation spectroscopy of pseudomorphic Al0.32Ga0.68As/In0.15Ga0.85As/GaAs high electron mobility transistor structures. Applied Physics Letters, 1993, 63, 1417-1419.	1.5	34
173	Characterization of Pseudomorphic Hemt Structures by Modulation Spectroscopy. Materials Research Society Symposia Proceedings, 1993, 324, 205.	0.1	4
174	Structural study of InxGa1-xP/GaAs interfaces grown by MOMBE. Semiconductor Science and Technology, 1992, 7, A127-A130.	1.0	2
175	Alloy clustering and defect structure in the molecular beam epitaxy of In_{0.53}Ga_{0.47}As on silicon. Journal of Materials Research, 1992, 7, 2194-2204.	1.2	15
176	Electricâ€field dependence of interband transitions in In0.53Ga0.47As/In0.52Al0.48As single quantum wells by roomâ€temperature electrotransmittance. Journal of Applied Physics, 1992, 72, 1912-1917.	1.1	20
177	Asymmetric Fabry-Perot p-i-n multiple quantum well optical modulators grown on silicon and GaAs substrates. Superlattices and Microstructures, 1992, 12, 145-149.	1.4	1
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